

STRUCTURE	Silicon Monolithic	Integrated Circuit
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TYPE Positive and Negative Variable Linear Regulator

PRODUCT SERIES BD3985FV

FEATURES

1. Built-in positive (REG1) and negative (REG2) Linear Regulator for CCDs/ Variable output/ Low saturation voltage type.

2. Built-in Discharge circuit. Negative output voltage (REG2) turns off immediately, after STB turns off.

OABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Parameter	Symbol	Limit	Unit
Positive Supply Voltage	VCC	+18 ※1	۷
Negative Supply Voltage	VEE	-18 ※1	۷
Power Dissipation	Pd	380 ※2	mW
Operating Temperature Range	Topr	-40~+85	°C
Storage Temperature Range	Tstg	-55~+125	°C
Maximum Junction Temperature	Tjmax	125	°C

※1 Not to exceed Pd.

%2 Reduced by 3.8mW/°C over Ta=25°C ,during IC without heat sink operation.

OOPERATING CONDITIONS

Parameter	Symbol	Min	Max	Unit
Positive Supply Voltage	VCC	+6.0	+18.0	V
Negative Supply Voltage	VEE	-14.0	-6.0	V
REG1 Output Voltage	Vo1	+5.0	+16.0	V
REG2 Output Voltage	Vo2	-8.5	-5.0	V
Output Current 1	lo1	_	25	mA
Output Current 2	lo2	_	50	mA

% Vdropout(Reg1) \times lo(Reg1) + Vdropout(Reg2) \times lo(Reg2) not to exceed Pd=380mW.



OELECTRICAL CHARACTERISTICS (Unless otherwise specified, Ta=25°C, VCC=16.5V, VEE=-10V, Set REG1=15V, Set REG2=-7.5V)

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Parameter	Symbol	Limits		Unit	0 - u di ti - u -		
Paralleter	SYIIDUT	MIN	Тур	MAX	Unit	Conditions	
【Bias current】						·	
Bias Current (VCC)	ICC	_	500	850	μA	lo1=OmA	
Bias Current (VEE)	IEE	_	150	250	μA	lo2=OmA	
[STB]							
STB OFF Voltage	STBOFF	0	_	0.6	٧	lo1,2=0mA	
STB ON Voltage	STBON	1.6	—	3.5	۷	lo1,2=0mA	
STB OFF Bias Current (VEE)	IOFF	-	130	_	μ A	lo1,2=0mA	
STB ON Input Current	lin	10	30	60	μ A	VSTB=2V, Io1,2=0mA	
[Discharge block]							
Discharge Current	Idis	150	300	550	μA		
[REG1]							
CTL1 Voltage	Vctl1	1.372	1.400	1. 428	۷	lo1=10mA	
Dropout Voltage 1	$\Delta Vd1$	-	0. 25	0.35	۷	Vcc=14.2V, lo1=25mA	
Peak Output Current 1	lo1	25	—	_	mA		
Load Regulation 1	Vload1	-	100	_	mV	lo1=0~25mA	
Short - Circuit Output Current 1	lshort1	-	50	_	mA	Vo1=0V	
Ripple Rejection 1	R. R. 1	-	50	_	dB	f=120Hz, ein=1Vrms, lo1=2mA	
Temperature Coefficient of Output Voltage 1 st	Tcvo1	-	±0.02	-	%/°C	lo1=1mA, Tj=0∼125°C	
[REG2]							
CTL2 Voltage	Vctl1	-1. 275	-1.250	-1. 225	۷	lo2=10mA	
Dropout Voltage2	$\Delta Vd2$	1	0.35	0.45	٧	VEE=-7.1V, Io2=50mA	
Peak Output Current2	lo2	50	—		mA		
Load Regulation2	Vload2	_	100	-	mV	lo2=0~50mA	
Short - Circuit Output Current 2	lshort2	_	120	-	mA	Vo2=0V	
Ripple Rejection2	R. R. 2	_	50	-	dB	f=120Hz, ein=1Vrms, lo2=2mA	
Temperature Coefficient of Output Voltage 2 st	Tcvo2	_	±0.02	-	%/°C	lo2=1mA, Tj=0∼125°C	

◎ Discharge time

 $t=(\text{Reg2} \times \text{Co})/\text{Idis}$ [s]

Co:Reg2 Output capacitor(μ F)

(VEE=-10V) % Design Guarantee (Shipment inspection is not done on all products.) This product is not designed for protection against radio active rays.

OPHYSICAL DIMENSIONS . MARKING





OBLOCK DIAGRAM



Pin No.	Pin Name
1	REG1
2	VCC
3	REG2
4	VEE
5	CTL2
6	STB
7	GND
8	CTL1

OPIN No. • PIN NAME

*Refer to the Technical Note about the details of the application.

OOPERATING NOTES

1) Absolute maximum ratings

Use of the IC in excess of absolute maximum ratings such as the applied voltage or operating temperature range may result in IC damage. Assumptions should not be made regarding the state of the IC (short mode or open mode) when such damage is suffered. A physical safety measure such as a fuse should be implemented when use of the IC in a special mode where the absolute maximum ratings may be exceeded is anticipated.

2) VEE potential

Ensure a minimum VEE pin potential in all operating conditions.

3) Thermal design

Use a thermal design that allows for a sufficient margin in light of the power dissipation (Pd) in actual operating conditions.

4) Pin short and mistake mounting

Use caution when orienting and positioning the IC for mounting on printed circuit boards. Improper mounting may result in damage to the IC. Shorts between output pins and the power supply and GND pins caused by the presence of a foreign object may result in damage to the IC. Ensure a minimum GND pin potential in all operating conditions.

- Actions in strong magnetic field Keep in mind that the IC may malfunction in strong magnetic fields.
- 6) Testing on application boards

When testing the IC on an application board, connecting a capacitor to a pin with low impedance subjects the IC to stress. Always discharge capacitors after each process or step. Always turn the IC's power supply off before connecting it to or removing it from a jig or fixture during the inspection process. Ground the IC during assembly steps as an antistatic measure, and use similar caution when transporting or storing the IC.

7) This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P/N junctions are formed at the intersection of these P layers with the N layers of other elements to create a variety of parasitic elements. For example, when the resistors and transistors are connected to the pins as shown in the following figure,

OThe P/N junction functions as a parasitic diode when VEE > Pin A for the resistor or VEE > Pin B for the transistor (NPN). OSimilarly, when VEE > Pin B for the transistor (NPN), the parasitic diode described above combines with the N layer of other adjacent elements to operate as a parasitic NPN transistor.



The formation of parasitic elements as a result of the relationships of the potentials of different pins is an inevitable result of the IC's architecture. The operation of parasitic elements can cause interference with circuit operation as well as IC malfunction and damage. For these reasons, it is necessary to use caution so that the IC is not used in a way that will trigger the operation of parasitic elements, such as by the application of voltages lower than the VEE (P substrate) voltage to input pins. Keep in mind that the IC may malfunction in strong magnetic fields.



8) Ground patterns

When using both small signal and large current GND patterns, it is recommended to isolate the two ground patterns, placing a single ground point at the application's reference point so that the pattern wiring resistance and voltage variations caused by large currents do not cause variations in the small signal ground voltage. Be careful not to change the GND wiring pattern of any external parts, either.

9) Applications or inspection processes where the potentials of the VCC pin and other pins may be reversed from their normal states may cause damage to the IC's internal circuitry or elements. Use an output pin capacitance of $1,000 \,\mu$ F or lower in case VCC is shorted with the GND pin while the external capacitor is charged. It is recommended to insert a diode for preventing back current flow in series with VCC or bypass diodes between VCC and each pin.



10) Thermal shutdown circuit (TSD)

This IC incorporates a built-in TSD circuit for the protection from thermal destruction. The IC should be used within the specified power dissipation range. However, in the event that the IC continues to be operated in excess of its power dissipation limits, the attendant rise in the junction temperature (Tj) will trigger the TSD circuit to turn off all output power elements. The circuit automatically resets once the junction temperature (Tj) drops. Operation of the TSD circuit presumes that the IC's absolute maximum ratings have been exceeded. Application designs should never make use of the TSD circuit.

11) Overcurrent protection circuit (OCP)

The IC incorporates a built-in overcurrent protection circuit that operates according to the output current capacity. This circuit serves to protect the IC from damage when the load is shorted. The protection circuit is designed to limit current flow by not latching in the event of a large and instantaneous current flow originating from a large capacitor or other component. This protection circuits is effective in preventing damage due to sudden and unexpected accidents. However, the IC should not be used in applications characterized by the continuous operation or transitioning of the protection circuits. At the time of thermal designing, keep in mind that the current capacity has negative characteristics to temperatures.

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